

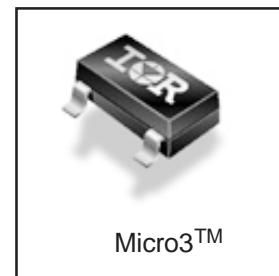
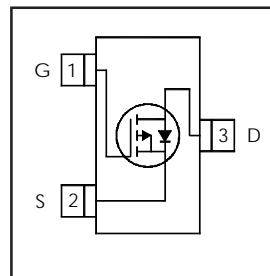
- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Low Gate Charge

$V_{DSS}$	$R_{DS(on)}$ max (m $\Omega$ )	$I_D$
<b>-30V</b>	98@ $V_{GS} = -10V$	-3.0A
	165@ $V_{GS} = -4.5V$	-2.6A

### Description

These P-channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.



### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain- Source Voltage	-30	V
$I_D$ @ $T_A = 25^\circ C$	Continuous Drain Current, $V_{GS}$ @ -10V	-3.0	A
$I_D$ @ $T_A = 70^\circ C$	Continuous Drain Current, $V_{GS}$ @ -10V	-2.4	
$I_{DM}$	Pulsed Drain Current ①	-24	
$P_D$ @ $T_A = 25^\circ C$	Power Dissipation	1.25	W
$P_D$ @ $T_A = 70^\circ C$	Power Dissipation	0.80	
	Linear Derating Factor	10	mW/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

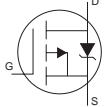
### Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ③	100	°C/W

Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.019	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}$ , $I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	98	m $\Omega$	$V_{GS} = -10V, I_D = -3.0A$ ②
		—	—	165		$V_{GS} = -4.5V, I_D = -2.6A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	-2.5	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$g_{fs}$	Forward Transconductance	3.1	—	—	S	$V_{DS} = -10V, I_D = -3.0A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-1.0	$\mu A$	$V_{DS} = -24V, V_{GS} = 0V$
		—	—	-5.0		$V_{DS} = -24V, V_{GS} = 0V, T_J = 70^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
$Q_g$	Total Gate Charge	—	9.5	14	nC	$I_D = -3.0A$
$Q_{gs}$	Gate-to-Source Charge	—	2.3	3.5		$V_{DS} = -24V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	1.6	2.4		$V_{GS} = -10V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = -15V$ ②
$t_r$	Rise Time	—	18	—		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	88	—		$R_G = 6.0\Omega$
$t_f$	Fall Time	—	52	—		$V_{GS} = -10V$
$C_{iss}$	Input Capacitance	—	510	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	71	—		$V_{DS} = -25V$
$C_{riss}$	Reverse Transfer Capacitance	—	43	—		$f = 1.0\text{MHz}$

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-24		
$V_{SD}$	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -1.3A, V_{GS} = 0V$ ②
$t_{rr}$	Reverse Recovery Time	—	17	26	ns	$T_J = 25^\circ\text{C}, I_F = -1.3A$
$Q_{rr}$	Reverse Recovery Charge	—	12	18	nC	$di/dt = -100A/\mu s$ ②

## Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .

③ Surface mounted on FR-4 board,  $t \leq 5\text{sec}$ .

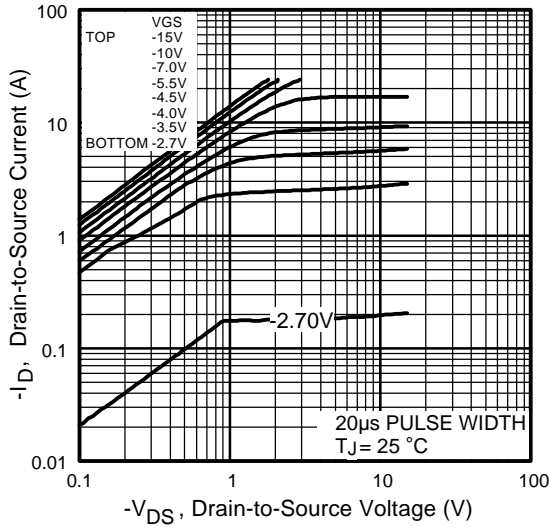


Fig 1. Typical Output Characteristics

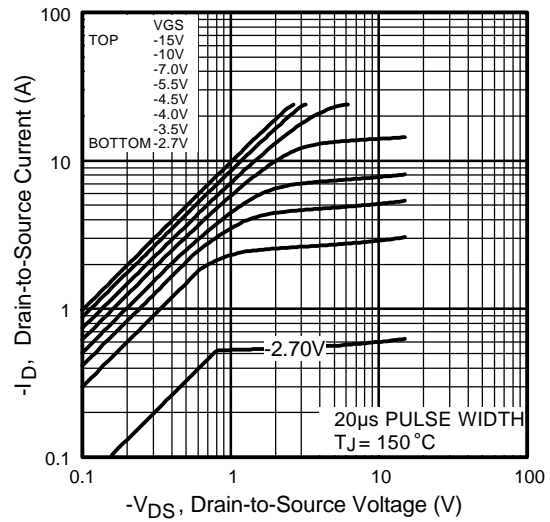


Fig 2. Typical Output Characteristics

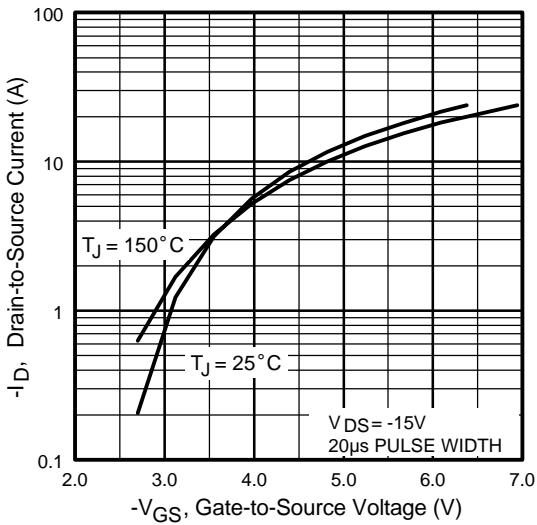


Fig 3. Typical Transfer Characteristics

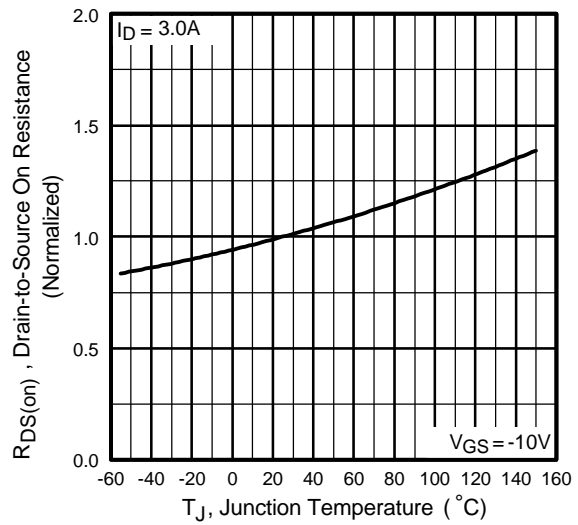
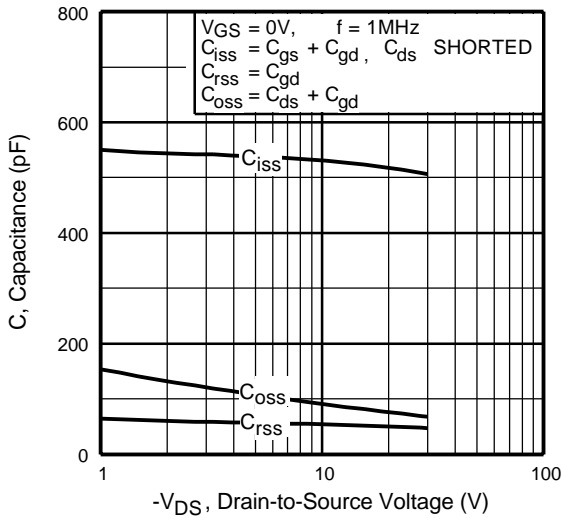
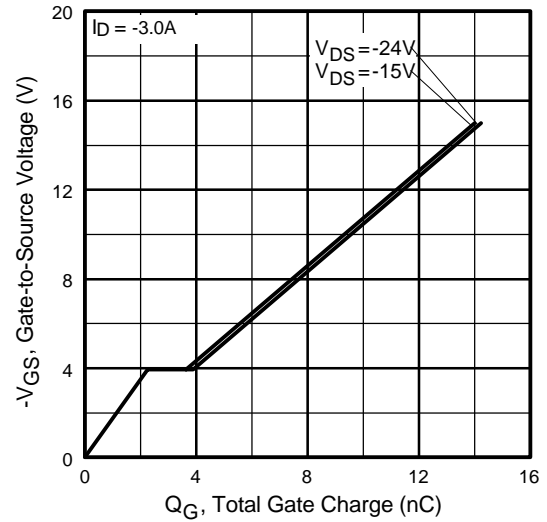


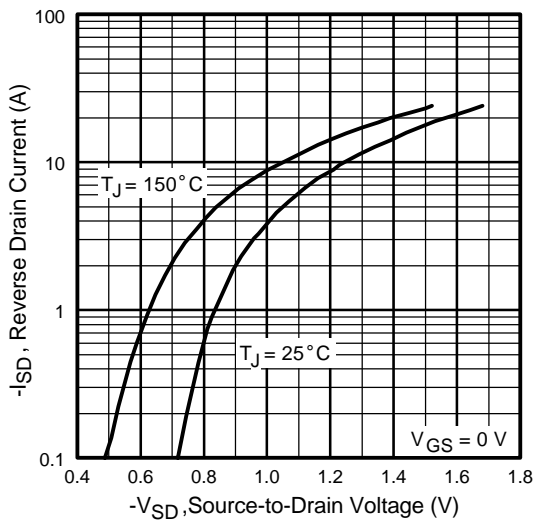
Fig 4. Normalized On-Resistance Vs. Temperature



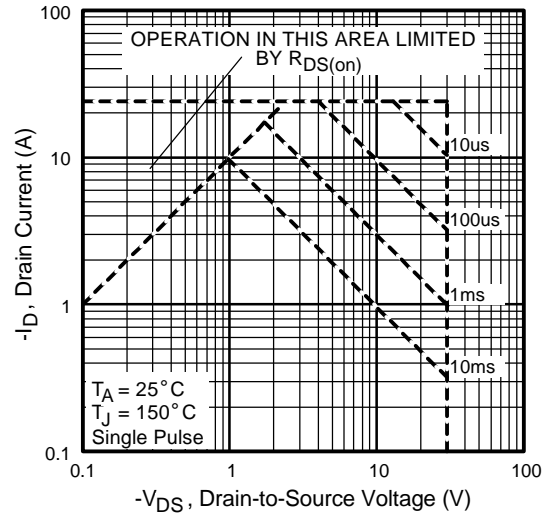
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

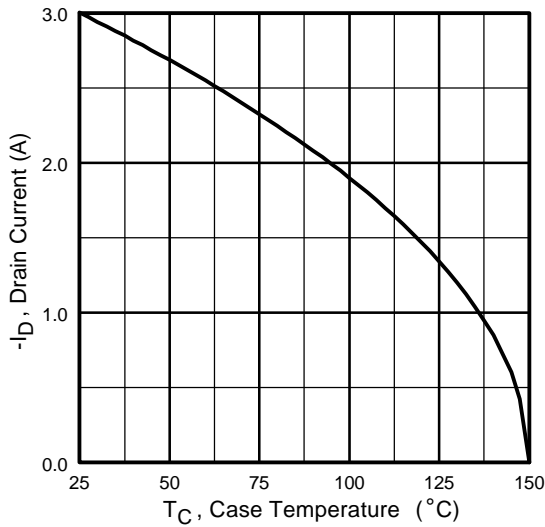


Fig 9. Maximum Drain Current Vs. Case Temperature

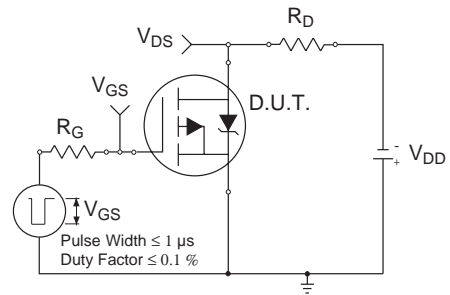


Fig 10a. Switching Time Test Circuit

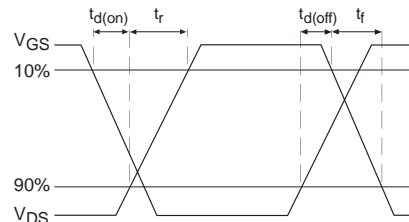


Fig 10b. Switching Time Waveforms

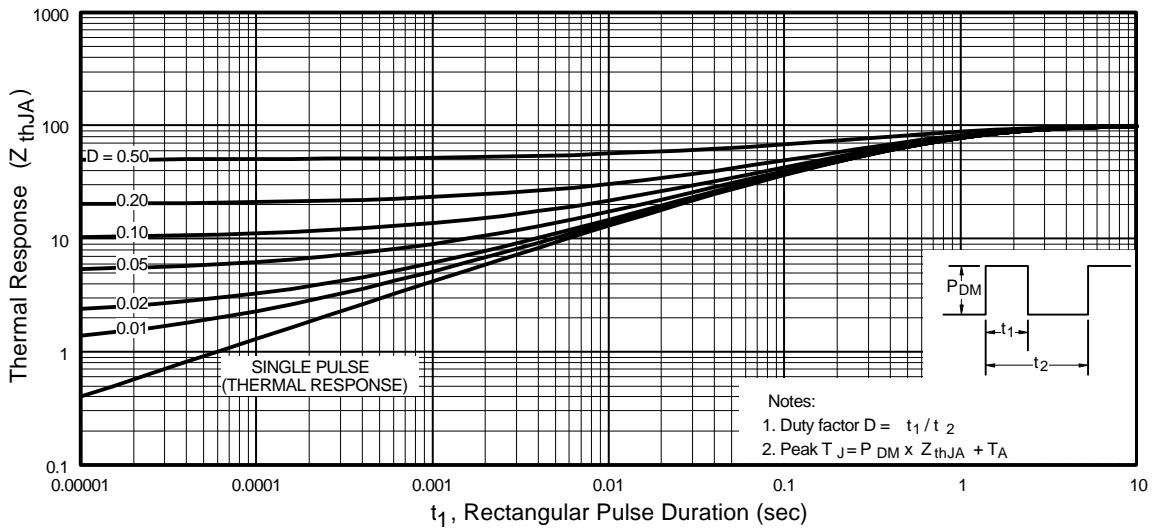
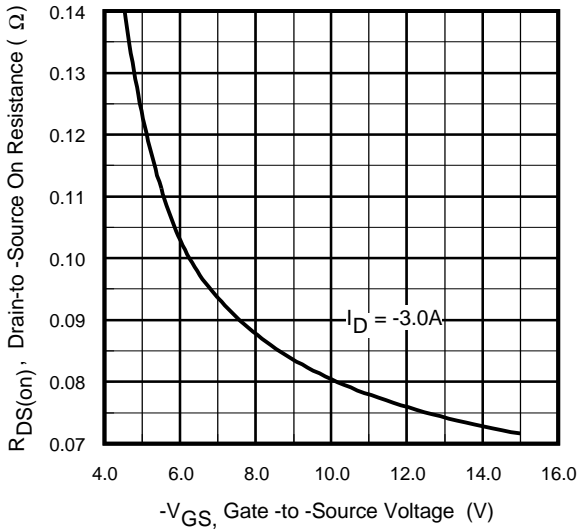
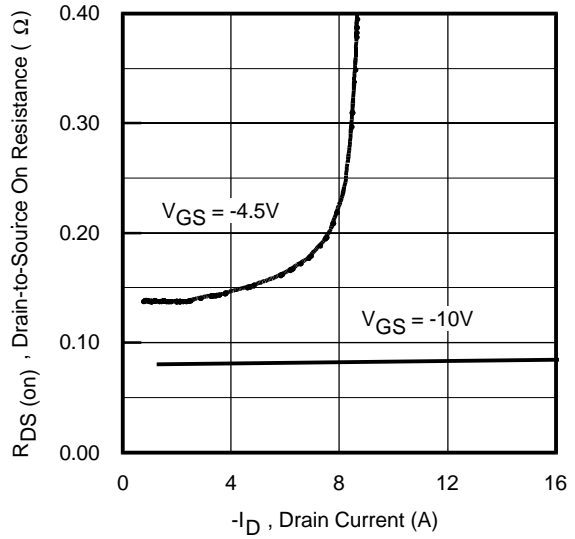


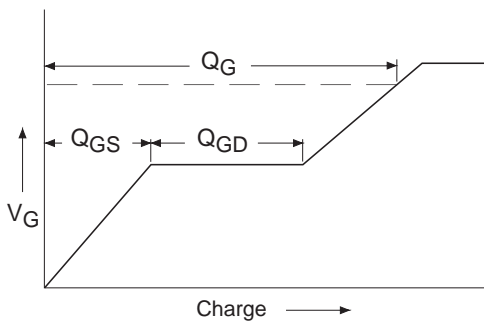
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



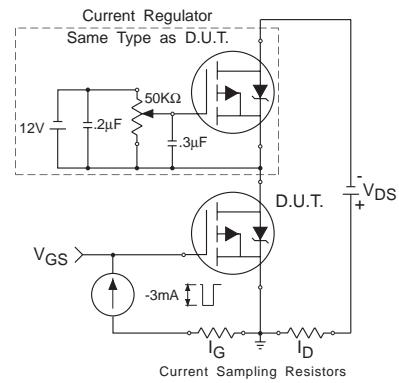
**Fig 11.** Typical On-Resistance Vs. Gate Voltage



**Fig 12.** Typical On-Resistance Vs. Drain Current



**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

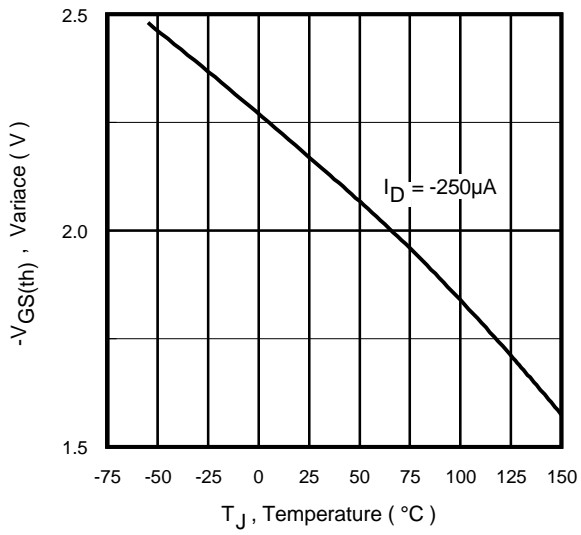


Fig 14. Threshold Voltage Vs. Temperature

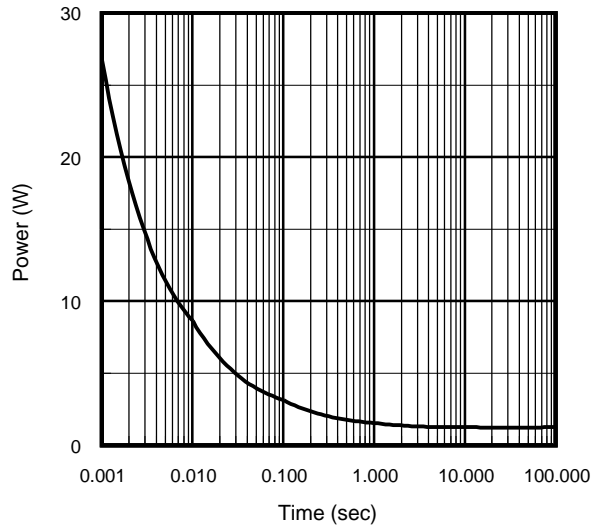


Fig 15. Typical Power Vs. Time

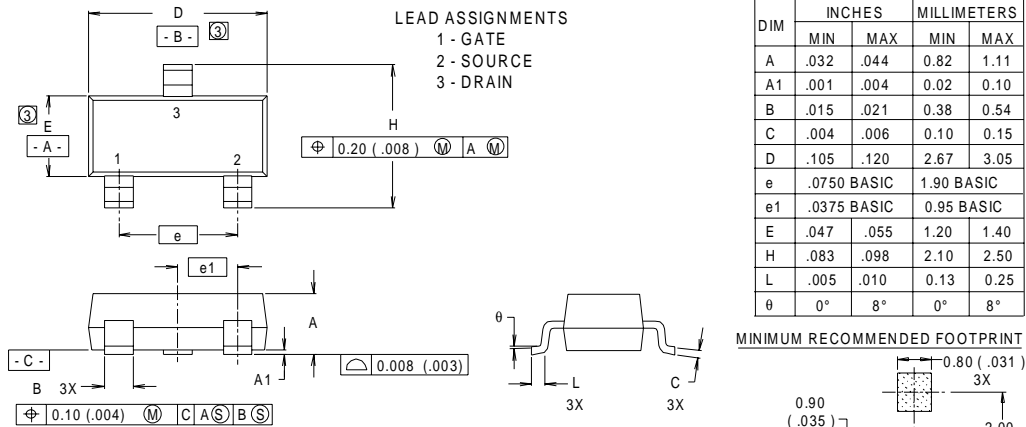
# IRLML5203

PROVISIONAL

International  
IRF Rectifier

## Micro3™ Package Outline

Dimensions are shown in millimeters (inches)

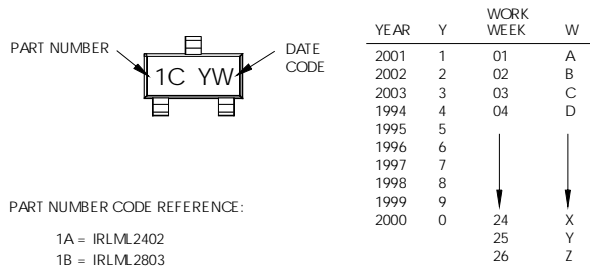


- NOTES:  
 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.  
 2. CONTROLLING DIMENSION : INCH.  
 ③ DIMENSIONS DO NOT INCLUDE MOLD FLASH.

## Micro3™ Part Marking Information

EXAMPLE: THIS IS AN IRLML6302

WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

- 1A = IRLML2402
- 1B = IRLML2803
- 1C = IRLML6302
- 1D = IRLML5103
- 1E = IRLML6402
- 1F = IRLML6401
- 1G = IRLML2502
- 1H = IRLML5203

DATE CODE EXAMPLES:

- YWW = 9503 = 5C
- YWW = 9532 = EF

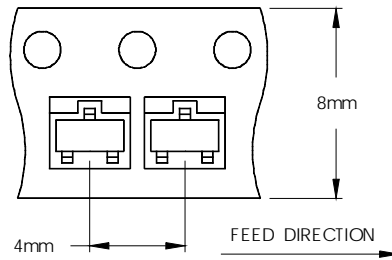
WW = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
1994	D	30	D
1995	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z



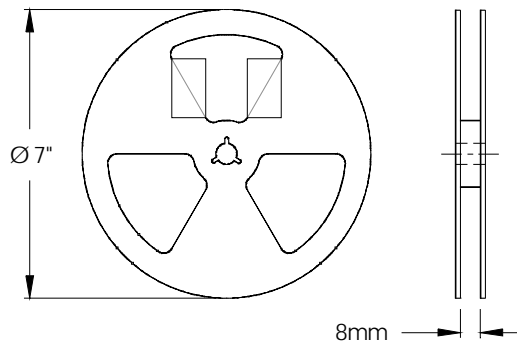
## Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.



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